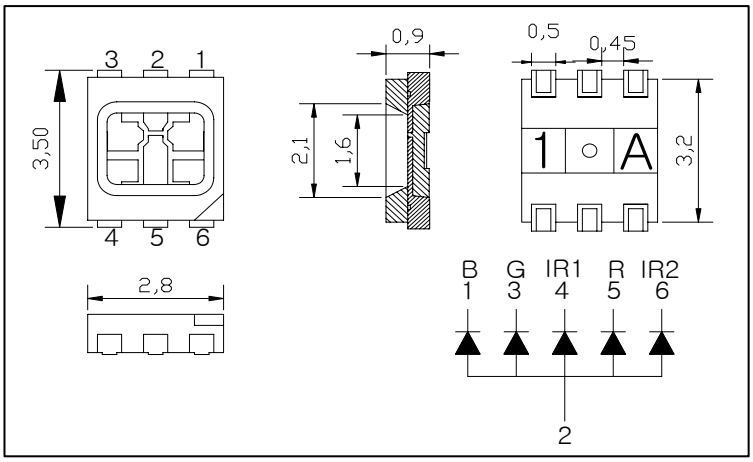
Light Emitting Diode(InGaAlP/InGaN/GaAsAl)

KLP-36M2I-X-X

KLP-34M2I is a 5 in 1 full colour LED and 2 ired .

DIMENSIONS



Features

- Transparent epoxy Encapsulent
- High Optical Output

Applications

- ATM
- SENSOR

Maximum Ratings [Ta=25˚C]

Parameter	Symbol		MIN	MAX	Unit	Conditions
Forward Current	I_F	R	-	20	mA	
		G	-	20	mA	
		B	-	20	mA	
		IR1	-	20	mA	
		IR2	-	20	mA	
Peak Forward Current*1	I_{FP}	R	-	80	mA	
		G	-	100	mA	
		B	-	100	mA	
Power Dissipation	P_D	R	-	55	mW	
		G	-	75	mW	
		B	-	75	mW	
		IR1	-	30	mW	
		IR2	-	30	mW	
Operating Temperature	T_{OP}		-30	85	°C	
Storage Temperature	Ts		-40	105	°C	
Soldering Temperature* 2	T_{sol}			260	°C	5 Sec

*1. I_{FP} Measured under duty £ 1/10 @ 1KHz

*2. Soldering time £ 5 Sec

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Electro-Optical Characteristics [Ta=25˚C]

Parameter	Symbol		MIN	TYP	MAX	Unit	Conditions
Forward Voltage	V_F	R	1.8	-	2.8	V	I_F=20mA
		G	2.8	-	3.8	V	I_F=20mA
		B	2.8	-	3.8	V	I_F=20mA
		IR1	-	1.2	-	V	I_F=20mA
		IR2	-	1.2	-	V	I_F=20mA
Luminous Intensity	P_O	R	9	13	17	mW	I_F=20mA
		G	5	10	15	mW	I_F=20mA
		B	15	21	27	mW	I_F=20mA
		IR1	3	7	11	mW	I_F=20mA
		IR2	2	5	8	mW	I_F=20mA
Dominant Wavelength	W_D	R	620	-	630	nm	I_F=20mA
		G	520	-	530	nm	I_F=20mA
		B	460	-	470	nm	I_F=20mA
Peak Wavelength	W_P	IR1	-	850	-	nm	I_F=20mA
		IR2	-	940	-	nm	I_F=20mA
Reverse Current	I_R	R	-	-	10	μA	V_R=5V
		G	-	-	10	μA	V_R=5V
		B	-	-	10	μA	V_R=5V
		IR1	-	-	10	μA	V_R=5V
		IR2	-	-	10	μA	V_R=5V
Spectrum Radiation Bandwidth	Δλ	R	-	20	-	nm	I_F=20mA
		G	-	30	-	nm	I_F=20mA
		B	-	30	-	nm	I_F=20mA
		IR1	-	50	-	nm	I_F=20mA
		IR2	-	50	-	nm	I_F=20mA
Half angle	ΔΘ			120		deg	I_F=20mA

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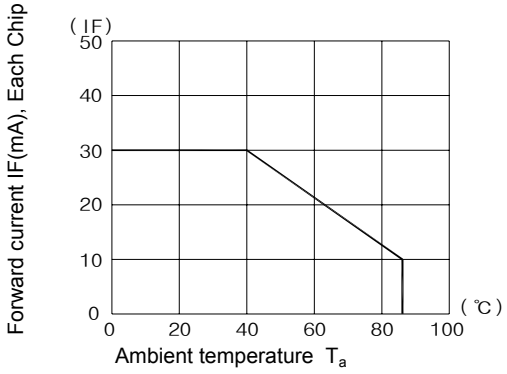
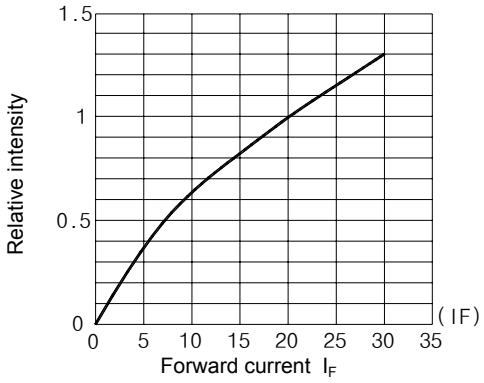
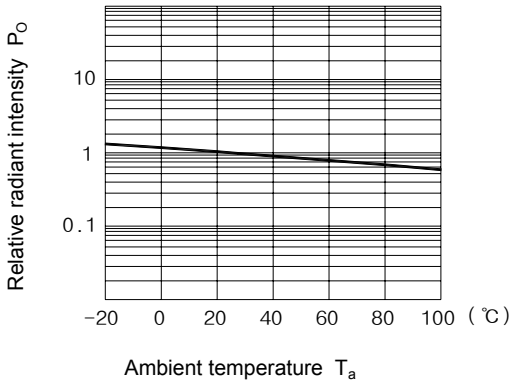
Forward current vs. Ambient temperature



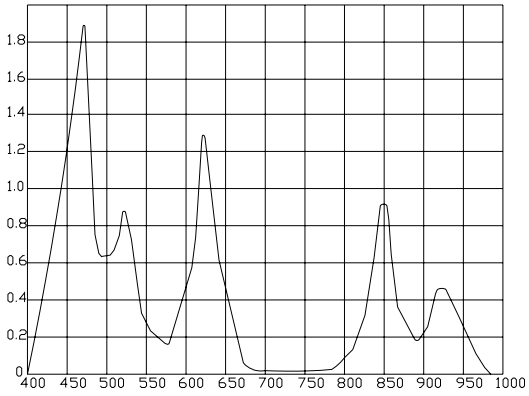
Radiant Intensity vs. Forward current



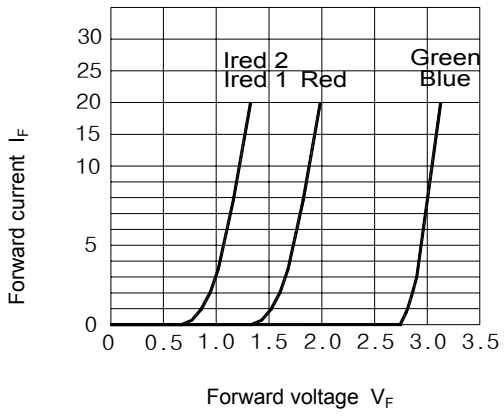
Relative radiant intensity vs. Ambient temperature



Relative intensity vs. Wavelength



Forward current vs. Forward voltage



Radiant Pattern

Angle(deg)